

~~DO NOT ENTER: J.M.A.~~

AMENDMENTS TO THE CLAIMS

1-16. (Cancelled)

17. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P and 0.01-5.0 mass % of at least one metallic element selected from Cu and Bi, and P, Cu and Bi having a purity of at least 99.9 %.

18. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P, 0.01-2.0 mass % of at least one metallic element selected from In, Sn and Zn, 0.01 to 0.9 mass % of Au and/or 0.01-5.0 mass % of Pd and/or 0.01-0.9 mass % of Pt, and P, In, Sn, Zn, Au, Pd and Pt having a purity of at least 99.9 %.

19. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P, 0.01-2.0 mass % of at least one metallic element selected from In, Sn and Zn, and 0.05-5.0 mass % of at least one metallic element selected from Cu, Ni, Fe and Bi, and P, In, Sn, Zn, Cu, Ni, Fe and Bi having a purity of at least 99.9 %.

20. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P, 0.01-0.9 mass % of Au, and 0.01-5.0 mass % of at least one metallic element selected from Cu and Bi, and P, Au, Cu and Bi having a purity of at least 99.9 %.

21. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0